L Number	Hits	Search Text	DB	Time stamp
-	69	(438/722).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 13:25
-	69	(("438/722").CCLS.) and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:27
-	223162	438/$.ccls. or 257/$.ccls. and @ad<=20010113	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 16:06
-	35716	(438/$.ccls. or 257/$.ccls. and @ad<=20010113) and 'dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 14:15
-	4864	((438/$.ccls. or 257/$.ccls. and @ad<=20010113) and 'dielectric') and 'mosfet'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 14:12
-	1	(((438/$.ccls. or 257/$.ccls. and @ad<=20010113) and 'dielectric') and 'mosfet') and 'group IV metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 14:14
-	16571	(438/$.ccls. or 257/$.ccls. and @ad<=20010113) and 'dielectric layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 14:21
-	61	((438/$.ccls. or 257/$.ccls. and @ad<=20010113) and 'dielectric layer') and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/27 16:46
-	104	((438/$.ccls. or 257/$.ccls. and @ad<=20010113) and 'dielectric') and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 14:25
-	36	((438/$.ccls. or 257/$.ccls. and @ad<=20010113) and 'dielectric') and 'amorphous oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 14:26
-	1	((438/$.ccls. or 257/$.ccls. and @ad<=20010113) and 'dielectric') and 'hafnium' and 'lanthanum' and 'amorphous oxides'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/14 14:26
-	224025	438/$.ccls. or 257/$.ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 11:50
-	15	(438/$.ccls. or 257/$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric metal oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/15 10:49
-	4906	(438/$.ccls. or 257/$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/15 10:51

-	73	((438/$.ccls. or 257/$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric') and 'hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 15:23
-	24	(((438/$.ccls. or 257/$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric') and 'hafnium') and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/15 10:55
-	2	("6020024").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/15 11:22
-	4	("4432035").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/15 13:44
-	417	(257/411).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/15 16:09
-	5	(("257/411").CCLS.) and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/15 13:46
-	230368	438/$.ccls. or 257/$.ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 11:54
-	168	(438/$.ccls. or 257/$.ccls. and @ad<=20010613) and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/23 12:14
-	2	(438/$.ccls. or 257/$.ccls. and @ad<=20010613) and 'hafnium' and 'combining' with 'oxygen'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 12:02
-	91	(438/$.ccls. or 257/$.ccls. and @ad<=20010613) and 'hafnium' with 'oxygen'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 12:07
-	67	'hafnium' with 'reaction' with 'oxygen'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 12:32
-	3	'hafnium oxide' near 'formation'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 12:33
-	58	(438/$.ccls. or 257/$.ccls. and @ad<=20010613) and 'silicon oxide' and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 15:42
-	51	(438/$.ccls. or 257/$.ccls. and @ad<=20010613) and 'metal' with 'reduces' with 'silicon oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 13:42

–	199	(438/785).ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:27
–	51	((438/785).ccls. and @ad<=20010613) and 'Hf'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 14:05
–	32	((438/785).ccls. and @ad<=20010613) and 'Hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 14:07
–	4	("4432035").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 14:32
–	1	"2693629".PN.	USPAT	2002/06/25 14:35
–	1	"3819990".PN.	USPAT	2002/06/25 14:35
–	1	"4062749".PN.	USPAT	2002/06/25 14:38
–	1	"4227944".PN.	USPAT	2002/06/25 14:38
–	1	"5106827".PN.	USPAT	2002/06/25 15:21
–	1	"5106827".PN.	USPAT	2002/06/25 15:21
–	1	"5187638".PN.	USPAT	2002/06/25 15:21
–	1	"5188902".PN.	USPAT	2002/06/25 15:21
–	1	"5273927".PN.	USPAT	2002/06/25 15:22
–	1	"6177361".PN.	USPAT	2002/06/25 15:22
–	1	"5824590".PN.	USPAT	2002/06/25 15:22
–	1	"5773314".PN.	USPAT	2002/06/25 15:22
–	1	"5572052".PN.	USPAT	2002/06/25 15:22
–	90	((438/$.ccls. or 257/$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric') and 'hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 16:05
–	0	@ad<=20010613 and 'reduces' with 'silicon dioxide to silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 15:44
–	1028	@ad<=20010613 and 'reduces' with 'silicon dioxide' with 'silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 15:47
–	29	@ad<=20010613 and 'reduces' adj 'silicon dioxide' with 'silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 16:01
–	4	@ad<=20010613 and 'hafnium' adj 'silicon dioxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 15:55
–	1	@ad<=20010613 and 'hafnium' adj 'silicon oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 15:55
–	126214	438/$.ccls. or 257/$.ccls. and @ad<=20010113 and 'high dielectric'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/25 16:09

–	124737	438/$.ccls. or 257/$.ccls. and @ad<=20010113 and 'high dielectric' and 'silicon oxide' and 'hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 08:52
–	31	@ad<=20010113 and 'PVD' with 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 11:45
–	393	@ad<=20010113 and 'high dielectric' and 'physical vapor deposition' or 'PVD' with 'ion bombarment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 09:01
–	393	@ad<=20010113 and 'high dielectric' and 'physical vapor deposition' or 'PVD' with 'ion bombarment energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 09:04
–	13419	@ad<=20010113 and 'high dielectric constant'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 09:08
–	332	(@ad<=20010113 and 'high dielectric constant') and 'physical vapor deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 09:09
–	0	((@ad<=20010113 and 'high dielectric constant') and 'physical vapor deposition') and 'ion bombardment energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 09:10
–	16	((@ad<=20010113 and 'high dielectric constant') and 'physical vapor deposition') and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 09:10
–	1	"4495219".PN.	USPAT	2002/07/11 10:00
–	1	"6013553".PN.	USPAT	2002/07/11 10:00
–	1	"6015739".PN.	USPAT	2002/07/11 10:00
–	1	"5464792".PN.	USPAT	2002/07/11 10:00
–	1	"6020024".PN.	USPAT	2002/07/11 10:01
–	1	"6020243".PN.	USPAT	2002/07/11 10:01
–	1	"6060755".PN.	USPAT	2002/07/11 10:01
–	1	"6110784".PN.	USPAT	2002/07/11 10:01
–	6	@ad<=20010113 and 'hafnium deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 11:46
–	22	@ad<=20010113 and 'hafnium' and 'PVD' and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 11:52
–	3	@ad<=20010113 and 'hafnium' and 'PVD' and 'ion bombardment' and 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 11:51
–	3	@ad<=20010113 and 'hafnium' and 'sputtering' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 13:13

-	53	@ad<=20010113 and 'metal' and 'sputtering' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 12:56
-	1	"4520413".PN.	USPAT	2002/07/11 13:08
-	1	"5930611".PN.	USPAT	2002/07/11 13:08
-	1	"6054331".PN.	USPAT	2002/07/11 13:09
-	1	"6060391".PN.	USPAT	2002/07/11 13:11
-	1	"6069070".PN.	USPAT	2002/07/11 13:12
-	266	@ad<=20010113 and 'hafnium' with 'sputtering'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/11 13:15
-	22	@ad<=20010113 and 'hafnium' and 'PVD' and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 12:01
-	22	@ad<=20010613 and 'hafnium' and 'PVD' and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 12:09
-	1	"4173661".PN.	USPAT	2002/07/23 12:08
-	1	"5773363".PN.	USPAT	2002/07/23 12:08
-	5	@ad<=20010613 and 'hafnium' and 'PVD' and 'ion bombardment' with 'energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:16
-	6	@ad<=20010613 and 'PVD' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 12:40
-	3	@ad<=20010613 and 'hafnium' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 12:52
-	29	@ad<=20010613 and 'PVD' and 'oxygen radical'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 12:38
-	67	@ad<=20010613 and 'sputter' and 'oxygen radical'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 12:39
-	19	@ad<=20010613 and 'hafnium' and 'sputter' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 12:50
-	4	@ad<=20010613 and 'hafnium' and 'sputter'and 'oxygen radical' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 12:44
-	6	@ad<=20010613 and 'hafnium' and 'Ionized' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 12:50

C:\APPS\east\workspaces\Dielectric Formation or SOG\09881408 HfO LaO dielectric layer.wsp

–		14	@ad<=20010613 and 'hafnium' and 'ion bombardment' and 'sputter' and 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:01
–		912	@ad<=20010613 and 'dielectric deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:10
–		118	(@ad<=20010613 and 'dielectric deposition') and 'refractory metal'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:09
–		1	((@ad<=20010613 and 'dielectric deposition') and 'refractory metal') and 'sputter' and 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:09
–		0	((@ad<=20010613 and 'dielectric deposition') and 'refractory metal') and 'PVD' and 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:09
–		12	(@ad<=20010613 and 'dielectric deposition') and 'hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:09
–		6	@ad<=20010613 and 'hafnium deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:15
–		96	@ad<=20010613 and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:19
–		3	(@ad<=20010613 and 'ion bombardment' with 'eV') and 'hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 13:20
–		2	("6399521").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 14:33
–		78	((438/$.ccls. or 257/$.ccls. and @ad<=20010113) and 'dielectric layer') and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/23 12:15
–		108	((438/$.ccls. or 257/$.ccls. and @ad<=20010113) and 'dielectric layer') and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:21
–		8	@ad<=20010113 and 'dielectric layer' and 'hafnium' and 'lanthanum' and 'oxygen' and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:33
–		29	@ad<=20010113 and 'physical vapor deposition' and 'hafnium' and 'oxygen' and 'ion bombardment'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:39

–		62	@ad<=20010113 and 'dielectric' and 'physical vapor deposition' and 'ion bombardment' same 'energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:40
–		120	@ad<=20010113 and 'physical vapor deposition' and 'ion bombardment' same 'energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:40
–	·	14	@ad<=20010113 and 'hafnium' and 'physical vapor deposition' and 'ion bombardment' same 'energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:53
–		2	@ad<=20010113 and 'lanthanum' and 'physical vapor deposition' and 'ion bombardment' same 'energy'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:41
–		14	@ad<=20010113 and 'physical vapor deposition' same 'hafnium oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:45
–		4	@ad<=20010113 and 'hafnium' and 'electron beam evaporation' and 'ion bombardment' and '10 eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 08:59
–		3	@ad<=20010113 and 'lanthanum' and 'electron beam evaporation' and 'ion bombardment' and '10 eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 09:37
–		2	@ad<=20010113 and 'lanthanum' and 'hafnium' and 'oxygen radical'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/24 09:40
–		2	("6387761").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 13:36
–		2	("6159855").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 13:38
–		2	("6013553").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 13:38
–	·	2178	@ad<=20010613 and 'Hafnium' same 'Lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 16:05
–		52	@ad<=20010613 and 'dielectric' with 'Hafnium' same 'Lanthanum'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 14:35
–		39	@ad<=20010613 and 'first' with 'Hf' same 'second' with 'La'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 14:42

C:\APPS\east\workspaces\Dielectric Formation or SOG\09881408 HfO LaO dielectric layer.wsp

–	274	@ad<=20010613 and 'first' with 'Group IV' and 'second' with 'Group III'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 14:45
–	16	@ad<=20010613 and 'first' with 'Group IVB' and 'second' with 'Group IIIB'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:06
–	243	(438/785).ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:35
–	83	(438/722).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:31
–	457	(257/411).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:31
–	597	(257/310).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:32
–	461	(257/410).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:35
–	158	(438/635).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:34
–	627	(438/778).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:35
–	400	(438/758).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:36
–	457	(257/411).CCLS. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:36
–	631	(438/240).ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:37
–	102	(438/216).ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:37
–	275	(438/591).ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:37

-		739	(438/585).ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 15:38
-		170	@ad<=20010613 and 'Hafnium oxide' with 'Lanthanum oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/21 16:24

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